Old Company Name in Catalogs and Other Documents

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April 1st, 2010 Renesas Electronics Corporation

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MOS FIELD EFFECT TRANSISTOR μ PA1890

N- AND P-CHANNEL MOS FIELD EFFECT TRANSISTOR FOR SWITCHING

DESCRIPTION

The μ PA1890 is a switching device which can be driven directly by a 4.0-V power source.

The μ PA1890 features a low on-state resistance and excellent switching characteristics, and is suitable for applications such as power switch of portable machine and so on.

FEATURES

- Can be driven by a 4.0-V power source
- · Low on-state resistance

N-Channel RDS(on)1 = 27 m Ω MAX. (VGS = 10 V, ID = 3.0 A) RDS(on)2 = 37 m Ω MAX. (VGS = 4.5 V, ID = 3.0 A) RDS(on)3 = 47 m Ω MAX. (VGS = 4.0 V, ID = 3.0 A) P-Channel RDS(on)1 = 37 m Ω MAX. (VGS = -10 V, ID = -2.5 A) RDS(on)2 = 56 m Ω MAX. (VGS = -4.5 V, ID = -2.5 A) RDS(on)3 = 64 m Ω MAX. (VGS = -4.0 V, ID = -2.5 A)

• Built-in G-S protection diode against ESD

ORDERING INFORMATION

PART NUMBER	PACKAGE
μPA1890GR-9JG	Power TSSOP8

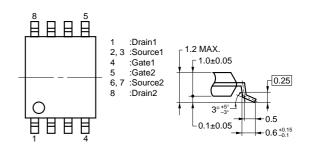
ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}C$)

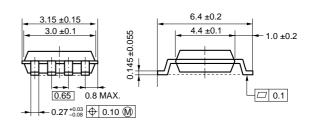
N-Channel / P-Channel Drain to Source Voltage **V**DSS 30/-30Gate to Source Voltage Vgss $\pm 20/\mp 20$ Drain Current (DC) ID(DC) $\pm 6.0/\mp 5.0$ Drain Current (pulse) Note1 ±24/∓20 Α D(pulse) Total Power Dissipation Note2 Рτ 2.0 Channel Temperature T_{ch} 150 °C -55 to +150 °C Storage Temperature Tsta

Notes 1. PW \leq 10 μ s, Duty Cycle \leq 1%

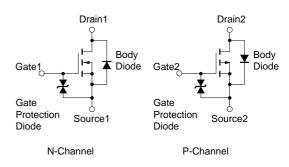
2. Mounted on ceramic substrate of 5000 mm² x 1.1 mm

PACKAGE DRAWING (Unit: mm)





EQUIVALENT CIRCUIT



To keep good radiate condition, it is recommended that all pins are soldering to print board.

Remark

The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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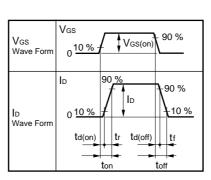


ELECTRICAL CHARACTERISTICS (TA = 25°C)

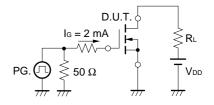
A) N-Channel

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Drain Cut-off Current	IDSS	V _{DS} = 30 V, V _{GS} = 0 V			-10	μΑ
Gate Leakage Current	lgss	$V_{GS} = \pm 16 \text{ V}, V_{DS} = 0 \text{ V}$			±10	μΑ
Gate Cut-off Voltage	V _{GS(off)}	V _{DS} = 10 V, I _D = 1 mA	1.5	1.8	2.5	٧
Forward Transfer Admittance	y fs	V _{DS} = 10 V, I _D = 3.0 A	3	7.6		S
Drain to Source On-state Resistance	RDS(on)1	V _G S = 10 V, I _D = 3.0 A		18	27	mΩ
	RDS(on)2	Vgs = 4.5 V, ID = 3.0 A		24	37	mΩ
	RDS(on)3	V _G S = 4.0 V, I _D = 3.0 A		27	47	mΩ
Input Capacitance	Ciss	V _{DS} = 10 V		748		pF
Output Capacitance	Coss	V _G S = 0 V		227		pF
Reverse Transfer Capacitance	Crss	f = 1 MHz		107		pF
Turn-on Delay Time	t _{d(on)}	V _{DD} = 15 V		20		ns
Rise Time	t r	ID = 3.0 A		80		ns
Turn-off Delay Time	t _{d(off)}	V _{GS(on)} = 10 V		48		ns
Fall Time	t f	$R_G = 10 \Omega$		30		ns
Total Gate Charge	Qg	V _{DD} = 24 V		14		nC
Gate to Source Charge	Qgs	ID = 6.0 A		1.9		nC
Gate to Drain Charge	Q _{GD}	V _{GS} = 10 V		3.8		nC
Diode Forward Voltage	V _{F(S-D)}	IF = 6.0 A, VGS = 0 V		0.82		V
Reverse Recovery Time	trr	IF = 6.0 A, VGS = 0 V		31	_	ns
Reverse Recovery Charge	Qrr	di/dt = 100 A/μs		32		nC

TEST CIRCUIT 1 SWITCHING TIME



TEST CIRCUIT 2 GATE CHARGE

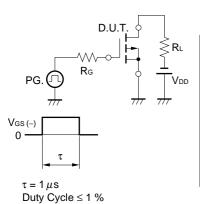


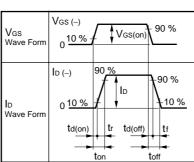


B) P-Channel

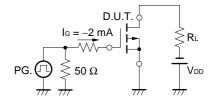
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Drain Cut-off Current	Ipss	V _{DS} = -30 V, V _{GS} = 0 V			-10	μΑ
Gate Leakage Current	lgss	$V_{GS} = \mp 16 \text{ V}, V_{DS} = 0 \text{ V}$			∓ 10	μΑ
Gate Cut-off Voltage	V _{GS(off)}	V _{DS} = -10 V, I _D = -1 mA	-1.3	-1.8	-2.3	V
Forward Transfer Admittance	y fs	$V_{DS} = -10 \text{ V}, I_{D} = -2.5 \text{ A}$	3	7.8		S
Drain to Source On-state Resistance	RDS(on)1	$V_{GS} = -10 \text{ V}, I_D = -2.5 \text{ A}$		28	37	mΩ
	RDS(on)2	$V_{GS} = -4.5 V, I_D = -2.5 A$		42	56	mΩ
	RDS(on)3	V _{GS} = -4.0 V, I _D = -2.5 A		47	64	mΩ
Input Capacitance	Ciss	V _{DS} = -10 V		851		pF
Output Capacitance	Coss	$V_{GS} = 0 V$		279		pF
Reverse Transfer Capacitance	Crss	f = 1 MHz		128		pF
Turn-on Delay Time	td(on)	V _{DD} = -15 V		17		ns
Rise Time	tr	I _D = -2.5 A		52		ns
Turn-off Delay Time	td(off)	$V_{GS(on)} = -10 \text{ V}$		84		ns
Fall Time	tf	$R_G = 10 \Omega$		73		ns
Total Gate Charge	Qg	V _{DD} = -24 V		15		nC
Gate to Source Charge	Qgs	I _D = -5.0 A		1.9		nC
Gate to Drain Charge	Q _{GD}	Vgs = -10 V		4.2		nC
Diode Forward Voltage	VF(S-D)	IF = 5.0 A, VGS = 0 V		0.83		V
Reverse Recovery Time	trr	IF = 5.0 A, VGS = 0 V		38		ns
Reverse Recovery Charge	Qrr	di/dt = 50 A/μs		35		nC

TEST CIRCUIT 1 SWITCHING TIME





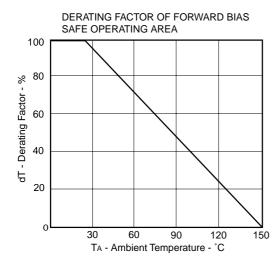
TEST CIRCUIT 2 GATE CHARGE

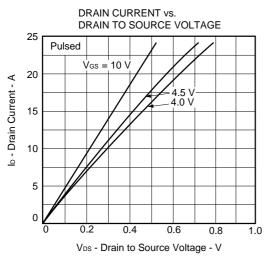


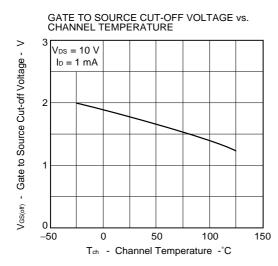


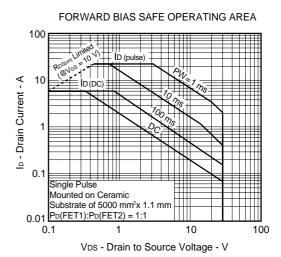
TYPICAL CHARACTERISTICS (TA = 25°C)

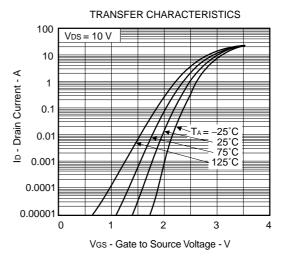
A) N-Channel

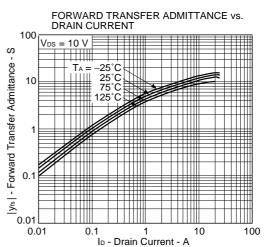


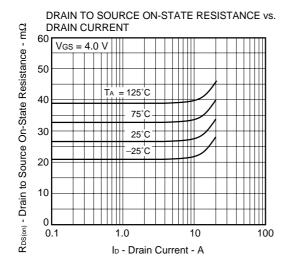


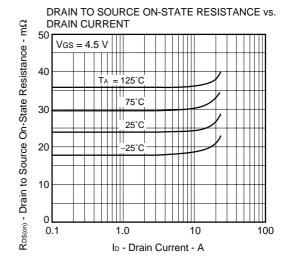


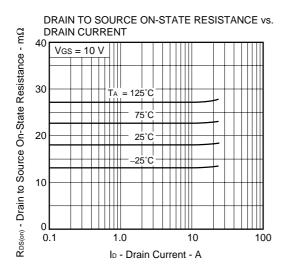


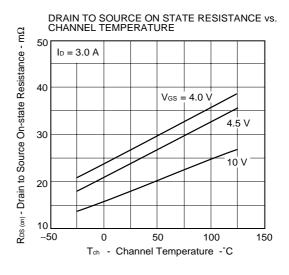


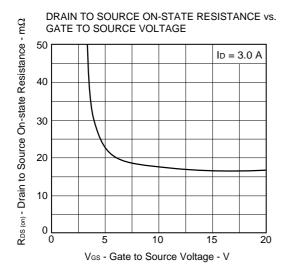


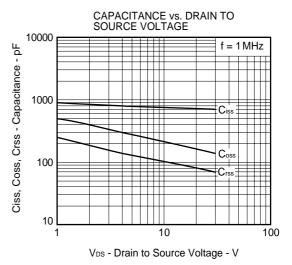






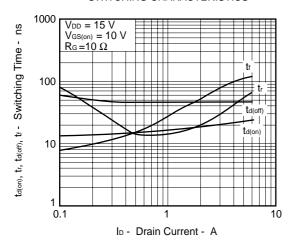




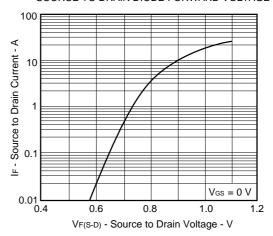


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SWITCHING CHARACTERISTICS

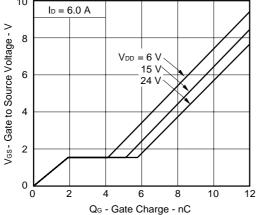


SOURCE TO DRAIN DIODE FORWARD VOLTAGE

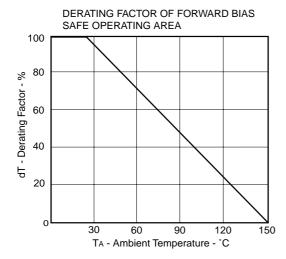


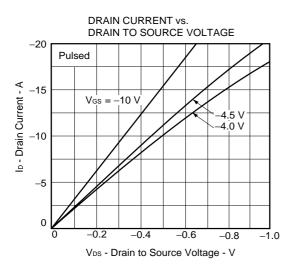
10 $I_D = 6.0 A$

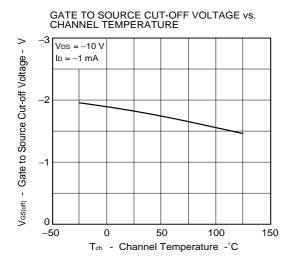
DYNAMIC INPUT CHARACTERISTICS

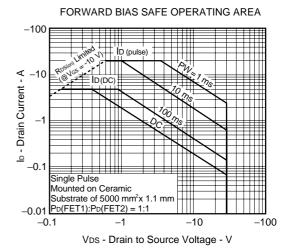


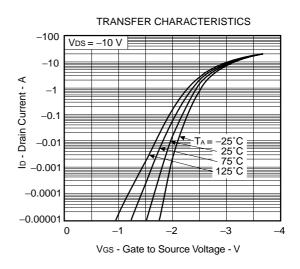
B) P-Channel

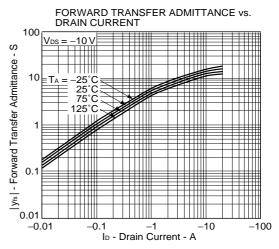




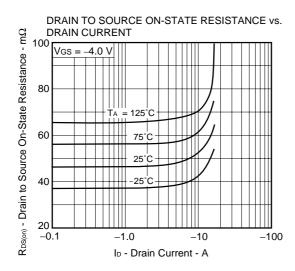


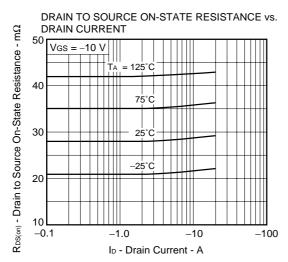


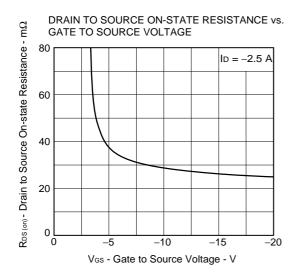


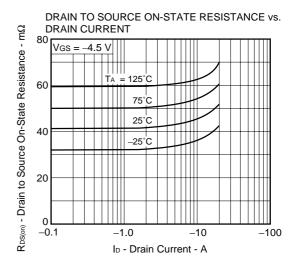


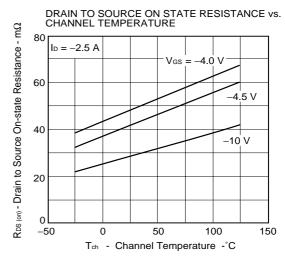
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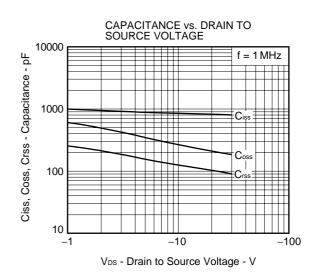




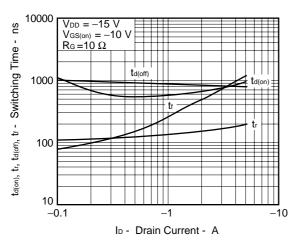




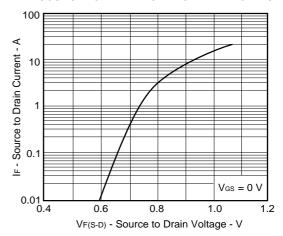


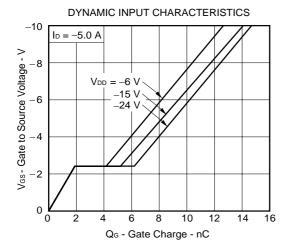


SWITCHING CHARACTERISTICS



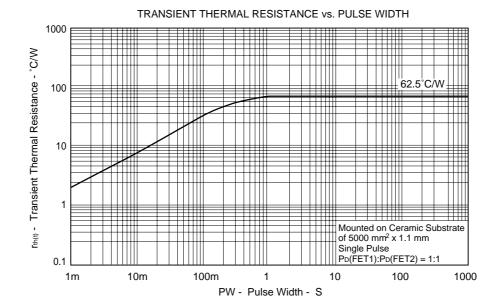
SOURCE TO DRAIN DIODE FORWARD VOLTAGE





C) Common

×



NEC μ PA1890

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